

MOSFETs Silicon N-channel MOS (U-MOSVIII)

TPN4R203NC

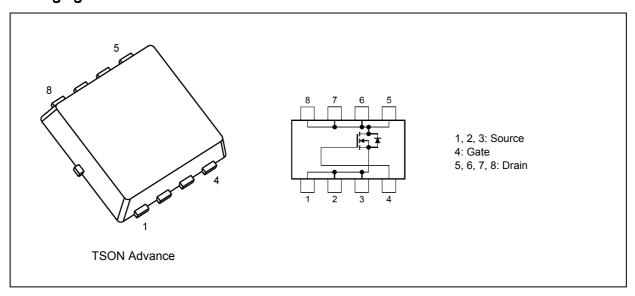
1. Applications

- · Lithium-Ion Secondary Batteries
- · Power Management Switches

2. Features

- (1) Small, thin package
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 3.5 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (3) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- (4) Enhancement mode: V_{th} = 1.3 to 2.3 V (V_{DS} = 10 V, I_{D} = 0.2 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25°C unless otherwise specified)

Characterist	ics		Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	30	V
Gate-source voltage			V _{GSS}	±20	
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I _D	53	Α
Drain current (DC)		(Note 1)	I _D	23	
Drain current (pulsed)	(1 ms)	(Note 1)	I _{DP}	146	
Power dissipation	(T _c = 25°C)		P_{D}	22	W
Power dissipation	(t = 10 s)	(Note 3)	P_{D}	1.9	
Power dissipation	(t = 10 s)	(Note 4)	P_{D}	0.7	
Single-pulse avalanche energy		(Note 5)	E _{AS}	62	mJ
Avalanche current			I _{AR}	23	Α
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



5. Thermal Characteristics

Characteristics				Max	Unit
Channel-to-case thermal resistance	$(T_c = 25^{\circ}C)$		R _{th(ch-c)}	5.68	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R _{th(ch-a)}	65.7	
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 4)	R _{th(ch-a)}	178	

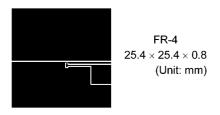
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Limited by silicon chip capability. Package limit is 45 A.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 0.091 mH, I_{AR} = 23 A



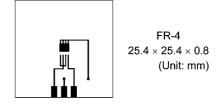


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_		±0.1	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	30			V
Drain-source breakdown voltage (Note 6)	V _{(BR)DSX}	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15			
Gate threshold voltage	V_{th}	$V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ mA}$	1.3	_	2.3	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 11.5 A	_	5.1	6.4	mΩ
		V _{GS} = 10 V, I _D = 11.5 A		3.5	4.2	

Note 6: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	_	1370	_	pF
Reverse transfer capacitance	C _{rss}		_	110	_	
Output capacitance	C _{oss}		_	420	_	
Switching time (rise time)	t _r	See Figure 6.2.1.	_	5.0	_	ns
Switching time (turn-on time)	t _{on}		_	13	_	
Switching time (fall time)	t _f]	_	14	_	
Switching time (turn-off time)	t _{off}		_	52	_	

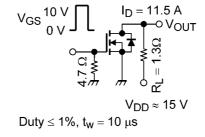


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 23 \text{ A}$	_	24	_	nC
Gate-source charge 1	Q _{gs1}		_	5	_	
Gate-drain charge	Q _{gd}		_	4.9	_	

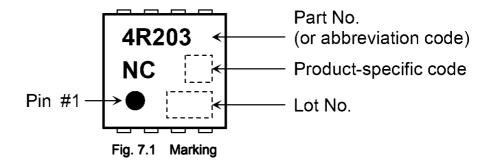
6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 7)	I _{DRP}	_	_	_	146	Α
Diode forward voltage		V_{DSF}	I _{DR} = 23 A, V _{GS} = 0 V	_	_	-1.2	V

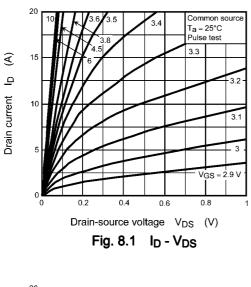
Note 7: Ensure that the channel temperature does not exceed 150°C.

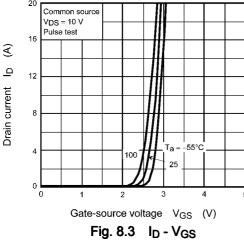


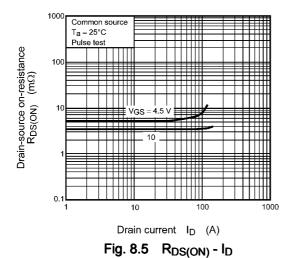
7. Marking

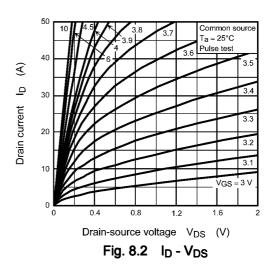


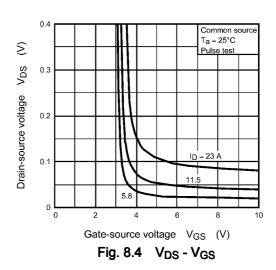
8. Characteristics Curves (Note)











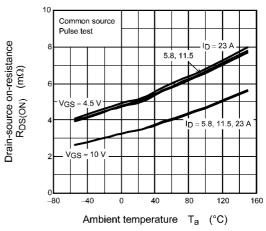


Fig. 8.6 R_{DS(ON)} - T_a

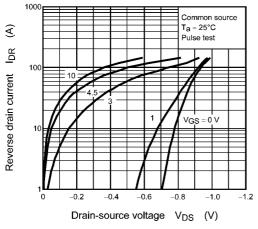


Fig. 8.7 IDR - VDS

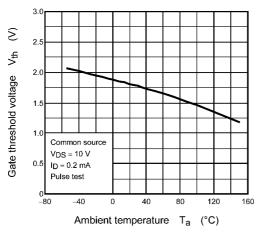
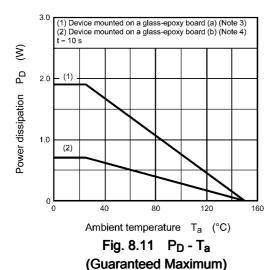


Fig. 8.9 V_{th} - T_a



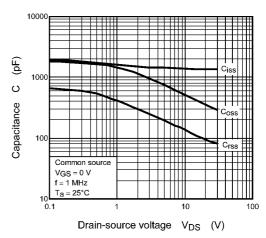


Fig. 8.8 Capacitance - V_{DS}

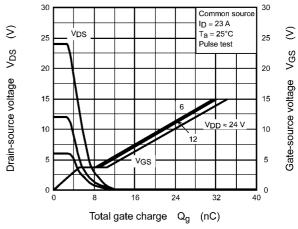


Fig. 8.10 Dynamic Input/Output Characteristics

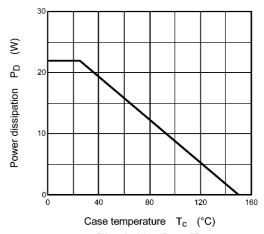


Fig. 8.12 P_D - T_c (Guaranteed Maximum)

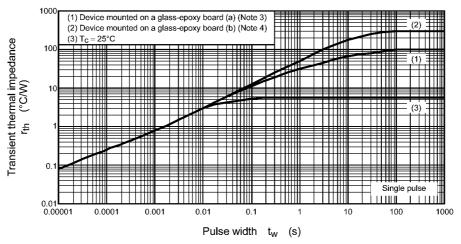


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

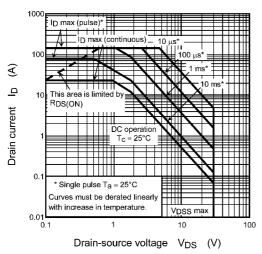


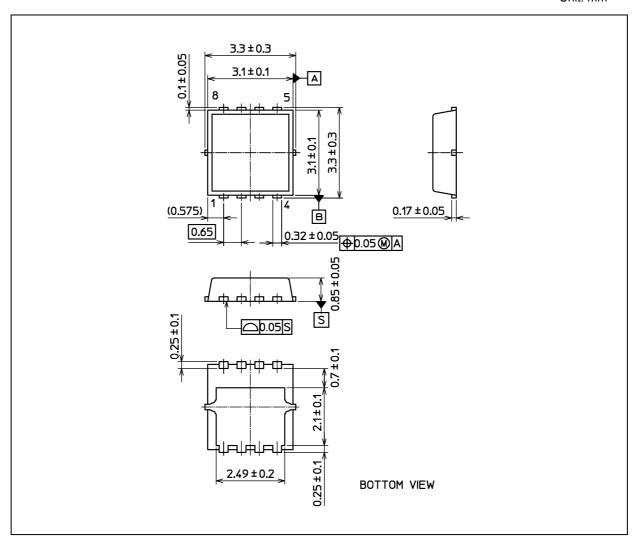
Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.02 g (typ.)

	Package Name(s)	
TOSHIBA: 2-3X1S		
Nickname: TSON A	dvance	



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